

resistance electrical contact between a metal and a layer of p-type CdTe surface by ion beam processing comprising:

- a) placing a CdS/CdTe device into a chamber and evacuating said chamber to create a vacuum;
- b) orientating the p-CdTe side of the CdS/CdTe device [so that it] to face[s] apparatus capable of generating Ar atoms and ions of preferred energy and directionality;
- c) introducing Argon and igniting the area of apparatus [capable of generating] to generate Ar atoms and ions of preferred energy and directionality in a manner so that during ion exposure, the source-to-substrate distance is maintained such that it is less than the mean-free path or diffusion length of the Ar atoms and ions at the vacuum pressure; and
- d) allowing exposure of the p-CdTe side of the layer to said ion beam for a period less than about 5 minutes.

4. (Amended) The process of claim [3] 2 wherein said mean-free path of the Ar atoms and ions are $>500\mu\text{m}$ and pressure of the vacuum is about $1\text{e}-5$ torr.

REMARKS

The Official Action and the cited references have been carefully reviewed. The review indicates that the claims, especially as amended, recite patentable subject matter and